

DATA SHEET

CGY2032BTS **DECT 500 mW power amplifier**

Preliminary specification
File under Integrated Circuits, IC17

2000 Mar 14

DECT 500 mW power amplifier

CGY2032BTS

FEATURES

- Power Amplifier (PA) overall efficiency 55%
- 27.5 dBm saturated output power at 3.2 V
- 0 dBm input power
- 40 dB linear gain
- Operation without negative supply
- Wide operating temperature range -30 to +85 °C
- SSOP16 package.

APPLICATIONS

- 1.88 to 1.9 GHz transceivers for DECT applications
- 2 GHz transceivers: Personal Handy phone System (PHS), Digital Cellular System (DCS) and Personal Communication Services (PCS).

GENERAL DESCRIPTION

The CGY2032BTS is a GaAs Monolithic Microwave Integrated Circuit (MMIC) power amplifier specifically designed to operate from 3.6 V battery supply. No negative supply voltage is required for operation.

QUICK REFERENCE DATA

SYMBOL	PARAMETER ⁽¹⁾	MIN.	TYP.	MAX.	UNIT
V _{DD}	positive supply voltage	-	3.2	-	V
I _{DD}	total drain current	-	350	-	mA
P _o	output power	-	27.5	-	dBm
T _{amb}	ambient temperature	-30	-	+85	°C

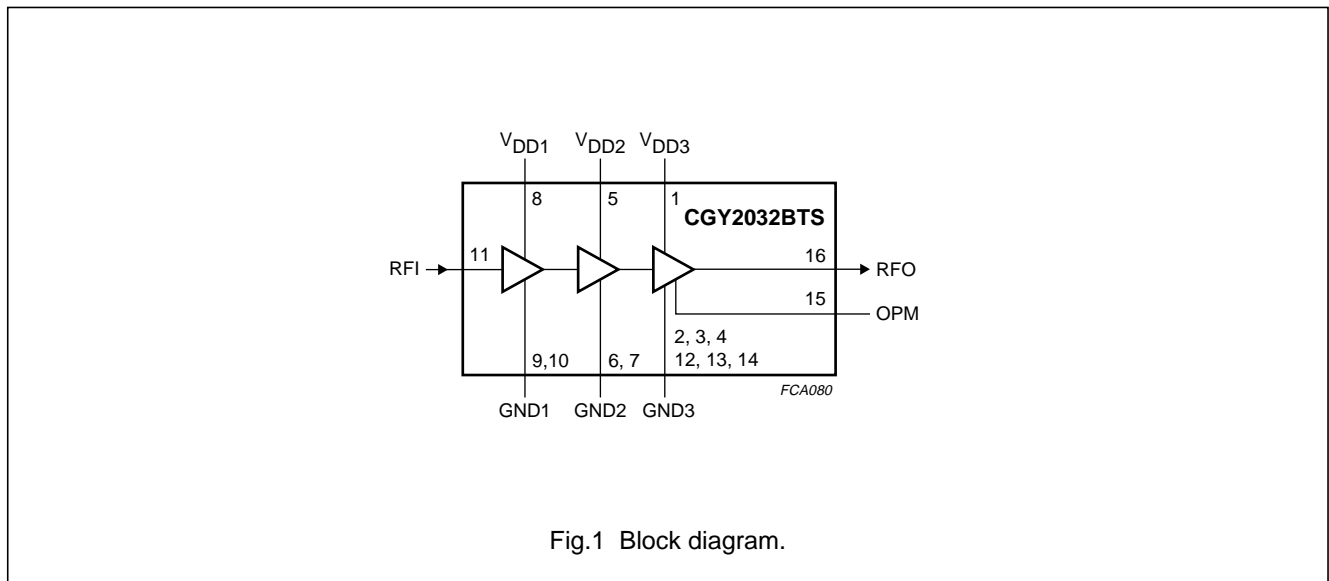
Note

1. For conditions, see Chapters "AC characteristics" and "DC characteristics".

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
CGY2032BTS	SSOP16	plastic shrink small outline package; 16 leads; body width 4.4 mm	SOT369-1

BLOCK DIAGRAM



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PINNING

SYMBOL	PIN	DESCRIPTION
V _{DD3}	1	third stage supply voltage
GND3	2	third stage ground supply
GND3	3	third stage ground supply
GND3	4	third stage ground supply
V _{DD2}	5	second stage supply voltage
GND2	6	second stage ground supply
GND2	7	second stage ground supply
V _{DD1}	8	first stage supply voltage
GND1	9	first stage ground supply
GND1	10	first stage ground supply
RFI	11	PA input
GND3	12	third stage ground supply
GND3	13	third stage ground supply
GND3	14	third stage ground supply
OPM	15	output pre-matching
RFO	16	PA output

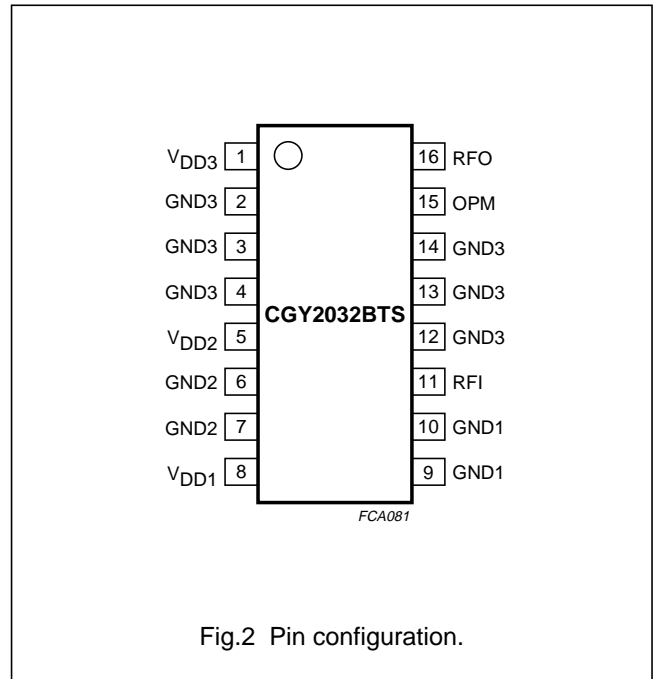


Fig.2 Pin configuration.

FUNCTIONAL DESCRIPTION

Amplifier

The CGY2032BTS is a 3-stage GaAs power amplifier capable of delivering 500 mW (typ.) at 1.9 GHz into a 50 Ω load. Each amplifier stage has an open-drain configuration. The drains have to be loaded externally by adequate reactive circuits which must also provide a DC path to the supply.

The amplifier can be switched off by means of a single external PNP or PMOS series switch connected between the battery and the amplifier drains.

This switch can also be used to vary the actual supply voltage applied to the amplifier and hence, control the output power.

This device is specifically designed to work with a duty factor of 50% and can work up to 100% with good thermal performance printed-circuit boards.

Biasing

Internal biasing is provided inside the amplifier for class AB operation.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DD}	operating supply voltage	note 1	–	5.2	V
T _{j(max)}	maximum operating junction temperature		–	150	°C
P _{tot}	total power dissipation	note 2	–	450	mW
P _i	input power		–	15	dBm
T _{stg}	storage temperature		–55	+125	°C

Notes

1. On Philips evaluation board.
2. On Philips evaluation board, P_{tot} maximum value is 600 mW.

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HANDLING

Do not operate or store near strong electrostatic fields. Meets class 1 ESD test requirements [Human Body Model (HBM)], in accordance with "MIL STD 883C - method 3015".

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	145	K/W

Note

1. On Philips evaluation board, $R_{th(j-a)}$ value is typically 80 K/W.

DC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Pins V_{DD1}, V_{DD2} and V_{DD3}						
V_{DD}	positive supply voltage		1.8	3.2	4.2	V
I_{DD0}	positive peak supply current	$V_{DD} = 3.2\text{ V}$	–	–	800	mA

AC CHARACTERISTICS

$V_{DD} = 3.2\text{ V}$; $f_{RF} = 1900\text{ MHz}$; $P_i = 0\text{ dBm}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; duty factor $\delta = 50\%$; $50\text{ }\Omega$ impedance system; measured and guaranteed on the CGY2032BTS evaluation board; the circuit diagram is shown in Fig.5.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
P_i	input power		–5	0	+5	dBm
δ	duty factor		–	50	100	%
P_o	output power	$V_{DD} = 3.2\text{ V}$	26.5	27.5	29	dBm
		$V_{DD} = 2.2\text{ V}$	24	25	27	dBm
I_{DD}	total drain current	$V_{DD} = 3.2\text{ V}$	–	350	500	mA
		$V_{DD} = 2.2\text{ V}$	–	–	400	mA
η	efficiency		–	55	–	%
P_{leak}	RF leakage to output in power off state	$V_{DD} = 0\text{ V}$	–	–40	–35	dBm
H2	second harmonic level		–	–	–30	dBc
H3	third harmonic level		–	–	–35	dBc
Stab	stability (spurious levels)	note 1	–	–60	–	dBc

Note

1. The device is adjusted to provide nominal load power into a $50\text{ }\Omega$ load. The device is switched off and a 3 : 1 load replaces the $50\text{ }\Omega$ load. The device is switched on and the phase of the 3 : 1 load is varied 360 electrical degrees during a 60 seconds test period.

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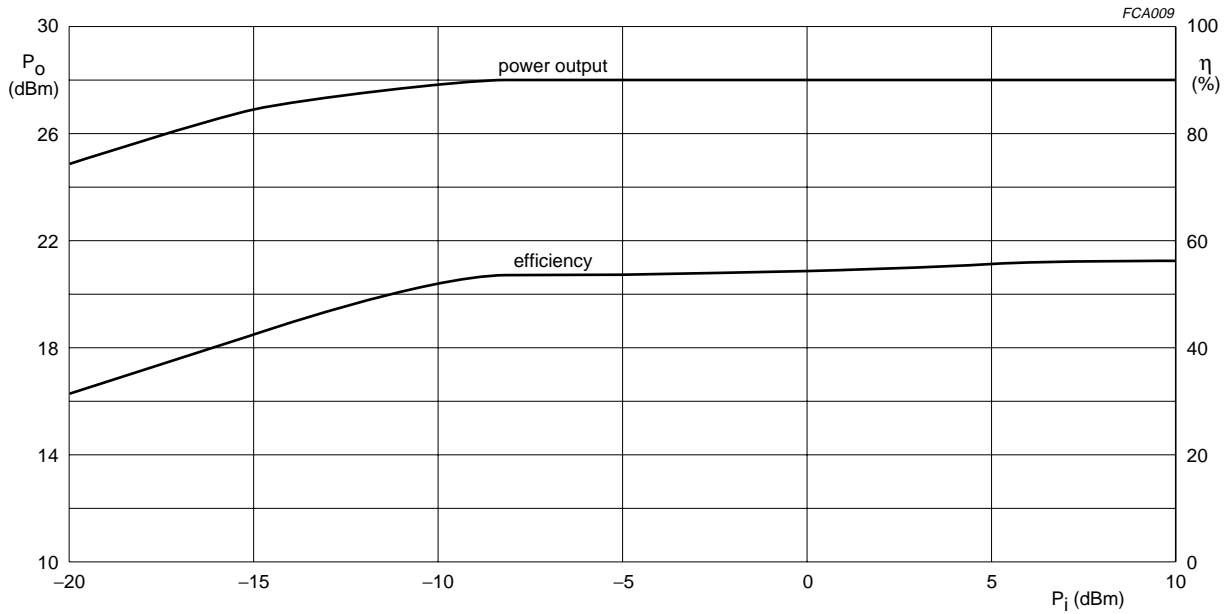


Fig.3 Typical output power and efficiency versus input power at $V_{DD} = 3.2$ V.

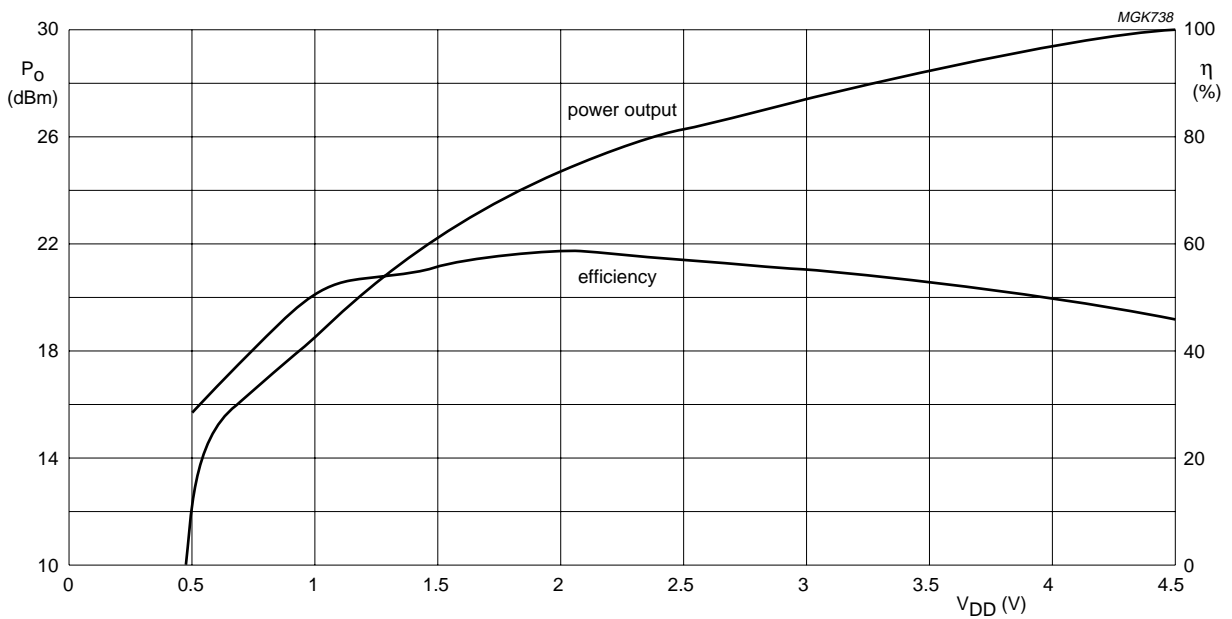


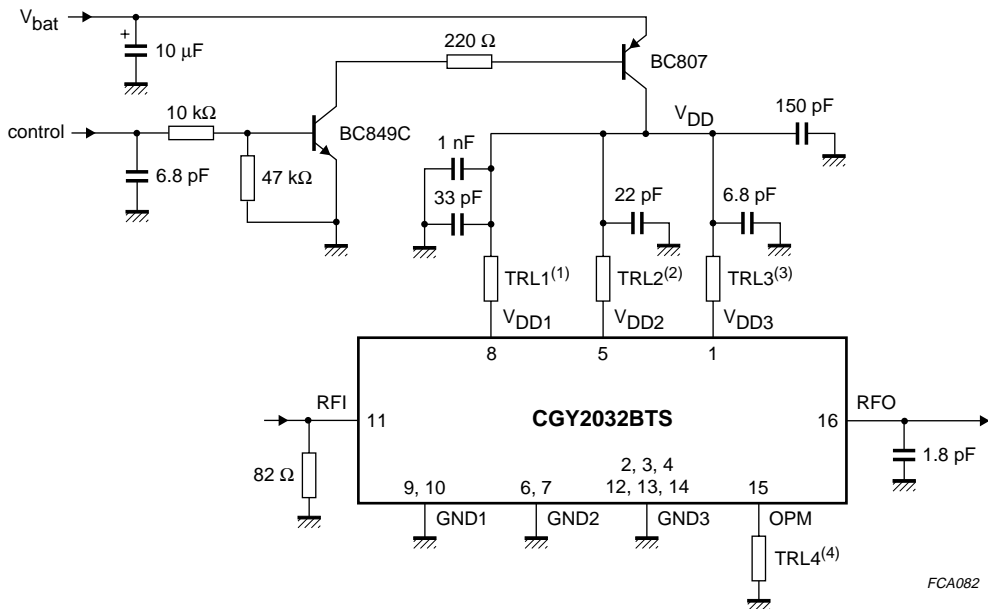
Fig.4 Typical output power and efficiency versus supply voltage at $P_i = 0$ dBm.

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APPLICATION INFORMATION

The CGY2032BTS is operated and tested in accordance with the circuit diagram shown in Fig.5. Supply voltage switching is achieved by a single bipolar PNP transistor.



Thickness: 0.8 mm; substrate: FR4; $\epsilon_r = 4.7$.

- (1) TRL1: width = 500 μm ; length = 10 mm.
- (2) TRL2: width = 500 μm ; length = 1 mm.
- (3) TRL3: width = 500 μm ; length = 8 mm.
- (4) TRL4: adjusted for optimum matching; width = 500 μm ; length = 1 to 3 mm.

Fig.5 Evaluation board circuit diagram.

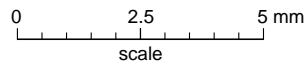
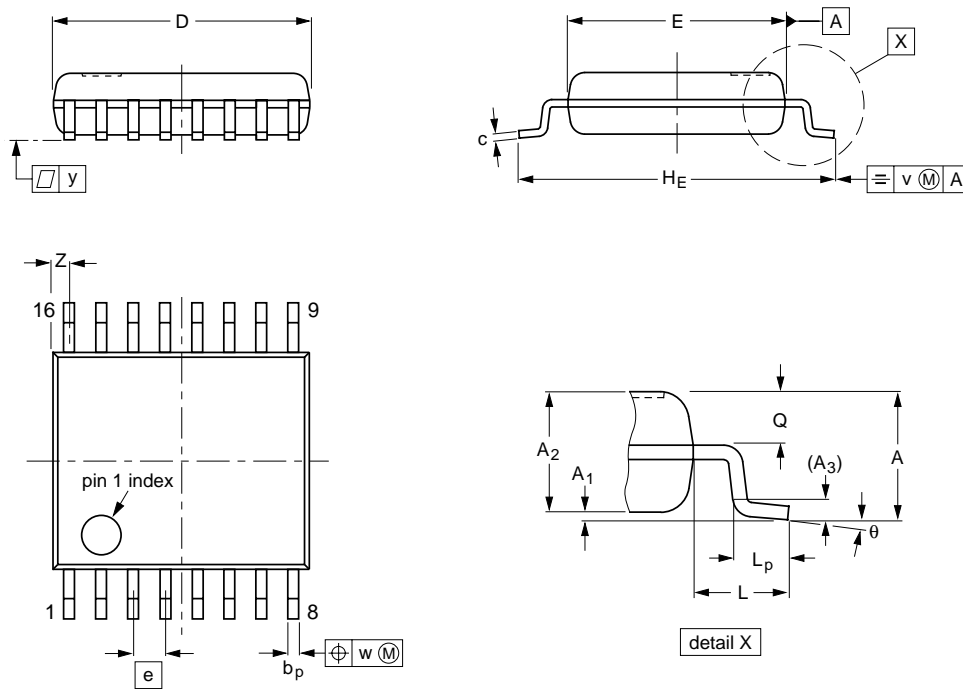
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PACKAGE OUTLINE

SSOP16: plastic shrink small outline package; 16 leads; body width 4.4 mm

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DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.5	0.15 0.00	1.4 1.2	0.25	0.32 0.20	0.25 0.13	5.30 5.10	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.45	0.65 0.45	0.2	0.13	0.1	0.48 0.18	10° 0°

Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT369-1		MO-152				95-02-04 99-12-27

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SOLDERING**Introduction to soldering surface mount packages**

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW ⁽¹⁾
BGA, SQFP	not suitable	suitable
HLQFP, HSQFP, HSOP, SMS	not suitable ⁽²⁾	suitable
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable

Notes

- All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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NOTES

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